

an Si film having a film thickness of 40 Å or less formed between the at least one light emitting end surface and the oxide protective coating.

2. (Amended) The semiconductor laser device as claimed in claim 1, wherein the Si film has a film thickness of from 5 Å to 30 Å.

3. (Amended) The semiconductor laser device as claimed in claim 1, wherein the oxide protective coating comprises Al_2O_3 .

4. (Unamended) The semiconductor laser device as claimed in claim 1, wherein the semiconductor laser chip has an active layer containing Al.

5. (Amended) The semiconductor laser device as claimed in claim 1, wherein the Si film has a silicon purity of 99.99% or more.

6. (Amended) A method for manufacturing the semiconductor laser device as claimed in claim 1, comprising forming the Si film and the oxide on the at least one light emitting end surface in succession within same equipment without exposing the surface to the air.

7. (Amended) A method for manufacturing the semiconductor laser device as claimed in claim 1, comprising forming the Si film and the oxide through vacuum deposition.

Please add the following new claims:

8. (New) The laser device of claim 1, wherein the oxide protective coating comprises Al_2O_3 .

9. (New) A semiconductor laser device, comprising:
a semiconductor laser chip;
a protective coating comprising Al_2O_3 formed on a light emitting end surface of the semiconductor laser chip; and
an intermediate film comprising silicon having a thickness of 40 Å or less formed between the light emitting end surface of the chip and the protective coating comprising Al_2O_3 .

REMARKS

This is in response to the Office Action dated August 14, 2002. New claims 8-9 have been added. Thus, claims 1-9 are now pending. Attached hereto is a marked-up version of the changes made to the claim(s) by the current amendment. The attached page(s) is captioned "Version With Markings To Show Changes Made."